Product Preview

Noninverting 3-State Buffer

The MC74VHC1G125 is an advanced high speed CMOS noninverting 3-state buffer fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

The internal circuit is composed of three stages, including a buffered 3–state output which provides high noise immunity and stable output.

The MC74VHC1G125 input structure provides protection when voltages up to 7V are applied, regardless of the supply voltage. This allows the MC74VHC1G125 to be used to interface 5V circuits to 3V circuits.

- High Speed: tpD = 3.5ns (Typ) at $V_{CC} = 5V$
- Low Power Dissipation: $I_{CC} = 2\mu A$ (Max) at $T_A = 25$ °C
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300mA
- ESD Performance: HBM > 1500V; MM > 200V

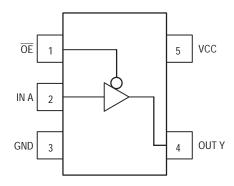


Figure 1. 5-Lead SOT-353 Pinout (Top View)

LOGIC SYMBOL





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SC-88A / SOT-353 DF SUFFIX CASE 419A

MARKING DIAGRAM



d = Date Code

| | PIN ASSIGNMENT | | | | | | | |
|---|----------------|--|--|--|--|--|--|--|
| 1 | ŌĒ | | | | | | | |
| 2 | IN A | | | | | | | |
| 3 | GND | | | | | | | |
| 4 | OUT Y | | | | | | | |
| 5 | VCC | | | | | | | |

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

FUNCTION TABLE

| A Input | OE Input | Y Output |
|---------|----------|----------|
| L | L | L |
| Н | L | Н |
| X | Н | Z |

This document contains information on a product under development. ON Semiconductor reserves the right to change or discontinue this product without notice.

MAXIMUM RATINGS*

| Characteristics | Symbol | Value | Unit |
|--|------------------|--|------|
| DC Supply Voltage | Vcc | -0.5 to +7.0 | V |
| DC Input Voltage | VIN | -0.5 to +7.0 | V |
| DC Output Voltage V _{CC} = 0 High or Low State | Vout | −0.5 to 7.0 −0.5 to V _{CC} + 0.5 | V |
| Input Diode Current | lık | -20 | mA |
| Output Diode Current $(V_{OUT} < GND; V_{OUT} > V_{CC})$ | lok | +20 | mA |
| DC Output Current, per Pin | lout | +25 | mA |
| DC Supply Current, V _{CC} and GND | Icc | +50 | mA |
| Power dissipation in still air, SC-88A † | PD | 200 | mW |
| Lead temperature, 1 mm from case for 10 s | TL | 260 | °C |
| Storage temperature | T _{stg} | -65 to +150 | °C |

^{*} Maximum Ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute—maximum—rated conditions is not implied. Functional operation should be restricted to the Recommended Operating Conditions.

RECOMMENDED OPERATING CONDITIONS

| Characteristics | Symbol | Min | Max | Unit |
|---|---------------------------------|-------------|-----------|------|
| DC Supply Voltage | Vcc | 2.0 | 5.5 | V |
| DC Input Voltage | VIN | 0.0 | 5.5 | V |
| DC Output Voltage | Vout | 0.0 | Vcc | V |
| Operating Temperature Range | TA | - 55 | +85 | °C |
| Input Rise and Fall Time $V_{CC} = 3.3V \pm 0.3V$ $V_{CC} = 5.0V \pm 0.5V$ | t _r , t _f | 0 | 100 20 | ns/V |

[†]Derating — SC-88A Package: -3 mW/°C from 65° to 125°C

DC ELECTRICAL CHARACTERISTICS

| | | | VCC | 1 | A = 25° | С | T _A ≤ | 85°C | T _A ≤ ' | 125°C | |
|-----------------|--|---|--------------------------|----------------------------|-------------------|----------------------------|----------------------------|----------------------------|----------------------------|----------------------------|------|
| Symbol | Parameter | Test Conditions | (V) | Min | Тур | Max | Min | Max | Min | Max | Unit |
| V _{IH} | Minimum High-Level Input Voltage | | 2.0 3.0 4.5 5.5 | 1.5 2.1 3.15 3.85 | | | 1.5 2.1 3.15 3.85 | | 1.5 2.1 3.15 3.85 | | V |
| V _{IL} | Maximum Low–Level Input Voltage | | 2.0 3.0 4.5 5.5 | | | 0.5 0.9 1.35 1.65 | | 0.5 0.9 1.35 1.65 | | 0.5 0.9 1.35 1.65 | V |
| VOH | Minimum High-Level Output Voltage V _{IN} = V _{IH} or V _{IL} | V _{IN} = V _{IH} or V _{IL} I _{OH} = -50μA | 2.0 3.0 4.5 | 1.9 2.9 4.4 | 2.0 3.0 4.5 | | 1.9 2.9 4.4 | | 1.9 2.9 4.4 | | V |
| | | $V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -4\text{mA}$ $I_{OH} = -8\text{mA}$ | 3.0 4.5 | 2.58 3.94 | | | 2.48 3.80 | | 2.34 3.66 | | V |
| VOL | Maximum Low–Level Output Voltage VIN = VIH or VIL | V _{IN} = V _{IH} or V _{IL} I _{OL} = 50μA | 2.0 3.0 4.5 | | 0.0 0.0 0.0 | 0.1 0.1 0.1 | | 0.1 0.1 0.1 | | 0.1 0.1 0.1 | V |
| | | VIN = VIH or VIL IOL = 4mA IOL = 8mA | 3.0 4.5 | | | 0.36 0.36 | | 0.44 0.44 | | 0.52 0.52 | V |
| loz | Maximum 3–State Leakage Current | V _{IN} = V _{IH} or V _{IL} V _{OUT} = V _{CC} or GND | 5.5 | | | ±0.25 | | ±2.5 | | ±2.5 | μА |
| IIN | Maximum Input V _{IN} = 5.5V or GND Leakage Current | | 0 to 5.5 | | | ±0.1 | | ±1.0 | | ±1.0 | μΑ |
| Icc | Maximum Quiescent Supply Current | V _{IN} = V _{CC} or GND | 5.5 | | | 2.0 | | 20 | | 40 | μΑ |

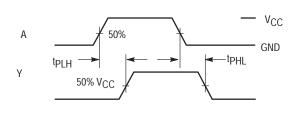
AC ELECTRICAL CHARACTERISTICS ($C_{load} = 50 \text{ pF}$, Input $t_r = t_f = 3.0 \text{ns}$)

| | | | 1 | A = 25°0 | | T _A ≤ | 85°C | T _A ≤ ' | 125°C | | |
|--|---|---|--|----------|------------|------------------|------|---------------------------|-------|--------------|------|
| Symbol | Parameter | Test Condi | Test Conditions | | Тур | Max | Min | Max | Min | Max | Unit |
| tPLH, tPHL | Maximum Propogation Delay, | $V_{CC} = 3.0 \pm 0.3 V$ | $C_L = 15 pF$ $C_L = 50 pF$ | | 4.5 6.4 | 8.0 11.5 | | 9.5 13.0 | | 12.0 16.0 | ns |
| | Input A to Y (Figures 2 and 4) | $V_{CC} = 5.0 \pm 0.5 V$ | $C_L = 15 pF$ $C_L = 50 pF$ | | 3.5 4.5 | 5.5 7.5 | | 6.5 8.5 | | 8.5 10.5 | |
| tPZL, tPZH | Maximum Output Enable Time, | $V_{CC} = 3.3 \pm 0.3 V$ $R_{L} = 1 k\Omega$ | C _L = 15 pF C _L = 50 pF | | 4.5 6.4 | 8.0 11.5 | | 9.5 13.0 | | 11.5 15.0 | ns |
| | Input OE to Y (Figures 3 and 5) | $V_{CC} = 5.0 \pm 0.5V$ $R_{L} = 1k\Omega$ | C _L = 15 pF C _L = 50 pF | | 3.5 4.5 | 5.1 7.1 | | 6.0 8.0 | | 8.5 10.5 | |
| t _{PLZ} , t _{PHZ} | Maximum Output Disable Time, | $V_{CC} = 3.3 \pm 0.3 V$ $R_L = 1 k\Omega$ | $C_L = 15 pF$ $C_L = 50 pF$ | | 6.5 8.0 | 9.7 13.2 | | 11.5 15.0 | | 14.5 18.0 | ns |
| | Input OE to Y (Figures 3 and 5) | $V_{CC} = 5.0 \pm 0.5V$ $R_L = 1k\Omega$ | $C_L = 15 pF$ $C_L = 50 pF$ | | 4.8 7.0 | 6.8 8.8 | | 8.0 10.0 | | 10.0 12.0 | |
| C _{IN} | Maximum Input Capacitance | | | | 4.0 | 10 | | 10 | | 10 | pF |
| COUT | Maximum 3–State Output Capacitance (Output in High Impedance State) | | | | 6.0 | | | | | | pF |

| | | Typical @ 25°C, V _{CC} = 5.0V | |
|----------|---|--|----|
| C_{PD} | Power Dissipation Capacitance (Note 1.) | 8.0 | pF |

^{1.} C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in}+I_{CC}. C_{PD} is used to determine the no–load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in}+I_{CC} • V_{CC}.

SWITCHING WAVEFORMS



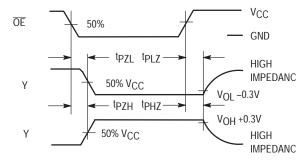
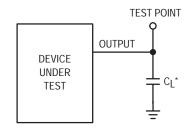
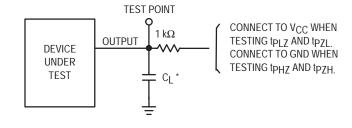


Figure 2.

Figure 3.





*Includes all probe and jig capacitance

Figure 4. Test Circuit

*Includes all probe and jig capacitance

Figure 5. Test Circuit

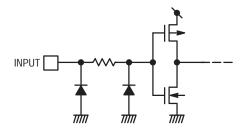


Figure 6. Input Equivalent Circuit

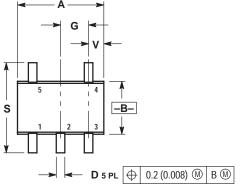
DEVICE ORDERING INFORMATION

| | Device Nomenclature | | | | | | | |
|---------------------|----------------------|-----------------------------|------------|--------------------|-------------------|--------------------------|---------------------|-----------------------|
| Device Order Number | Circuit Indicator | Temp Range Identifier | Technology | Device Function | Package Suffix | Tape & Reel Suffix | Package Type | Tape and Reel Size |
| MC74VHC1G125DFT1 | MC | 74 | VHC1G | 125 | DF | T1 | SC-88A / SOT-353 | 7–Inch/3000 Unit |

PACKAGE DIMENSIONS

SC-88A / SOT-353 **DF SUFFIX**

5-LEAD PACKAGE CASE 419A-01 ISSUE B

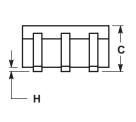


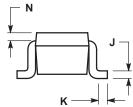
- NOTES:

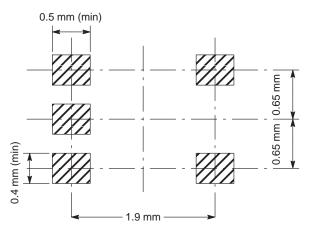
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MM.

| | INC | HES | MILLIN | IETERS |
|-----|-------------|-------|--------|--------|
| DIM | MIN | MAX | MIN | MAX |
| Α | 0.071 | 0.087 | 1.80 | 2.20 |
| В | 0.045 | 0.053 | 1.15 | 1.35 |
| С | 0.031 | 0.043 | 0.80 | 1.10 |
| D | 0.004 | 0.012 | 0.10 | 0.30 |
| G | 0.026 | BSC | 0.65 | BSC |
| Н | | 0.004 | | 0.10 |
| J | 0.004 | 0.010 | 0.10 | 0.25 |
| K | 0.004 | 0.012 | 0.10 | 0.30 |
| N | 0.008 | REF | 0.20 | REF |
| S | 0.079 0.087 | | 2.00 | 2.20 |
| V | 0.012 | 0.016 | 0.30 | 0.40 |







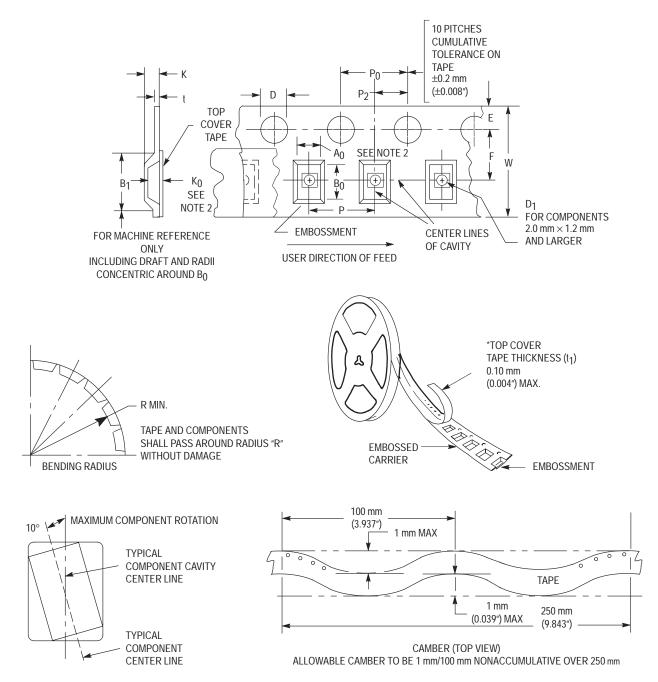


Figure 7. Carrier Tape Specifications

EMBOSSED CARRIER DIMENSIONS (See Notes 1 and 2)

| Tape Size | B ₁ Max | D | D ₁ | E | F | К | Р | P ₀ | P ₂ | R | Т | w |
|--------------|-----------------------|---|---------------------------|---------------------------------------|-------------------------------------|--------------------|---------------------------------------|--------------------------------------|--------------------------------------|------------------|---|--------------------------------------|
| 8 mm | 4.35 mm (0.171") | 1.5 +0.1/ -0.0 mm (0.059 +0.004/ -0.0") | 1.0 mm Min (0.039") | 1.75 ±0.1 mm (0.069 ±0.004") | 3.5 ±0.5 mm (1.38 ±0.002") | 2.4 mm (0.094") | 4.0 ±0.10 mm (0.157 ±0.004") | 4.0 ±0.1 mm (0.156 ±0.004") | 2.0 ±0.1 mm (0.079 ±0.002") | 25 mm (0.98") | 0.3 ±0.05 mm (0.01 +0.0038/ -0.0002") | 8.0 ±0.3 mm (0.315 ±0.012") |

^{1.} Metric Dimensions Govern-English are in parentheses for reference only.

^{2.} A₀, B₀, and K₀ are determined by component size. The clearance between the components and the cavity must be within 0.05 mm min to 0.50 mm max. The component cannot rotate more than 10° within the determined cavity

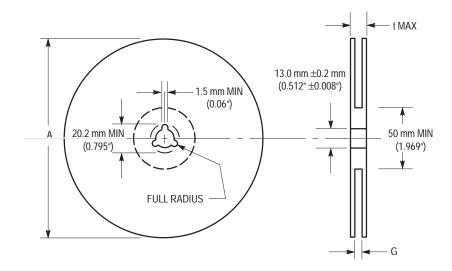


Figure 8. Reel Dimensions

REEL DIMENSIONS

| Tape Size | A Max | G | t Max |
|--------------|--------|-------------------------|---------|
| 8 mm | 330 mm | 8.400 mm, +1.5 mm, -0.0 | 14.4 mm |
| | (13") | (0.33", +0.059", -0.00) | (0.56") |

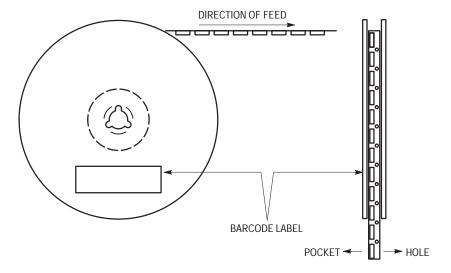


Figure 9. Reel Winding Direction

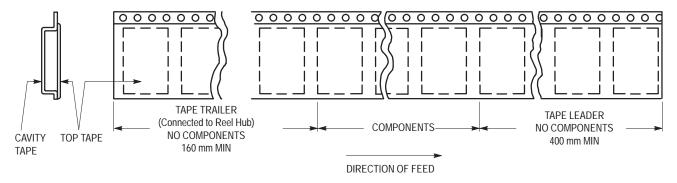


Figure 10. Tape Ends for Finished Goods

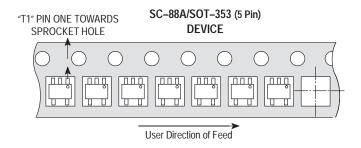


Figure 11. Reel Configuration

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